

Title (en)

COMPOSITIONS AND METHODS USING SAME FOR DEPOSITION OF SILICON-CONTAINING FILM

Title (de)

ZUSAMMENSETZUNGEN UND VERFAHREN MIT VERWENDUNG DAVON ZUR ABSCHIEDUNG VON SILICIUMHALTIGEM FILM

Title (fr)

COMPOSITIONS ET PROCÉDÉS UTILISANT DE TELLES COMPOSITIONS POUR LE DÉPÔT D'UN FILM CONTENANT DU SILICIUM

Publication

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Application

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Abstract (en)

[origin: US2019376178A1] Described herein are compositions and methods using same for forming a silicon-containing film such as without limitation a silicon carbide, silicon nitride, silicon oxide, silicon oxynitride, a carbon-doped silicon nitride, a carbon-doped silicon oxide, or a carbon doped silicon oxynitride film on at least a surface of a substrate having a surface feature. In one aspect, the silicon-containing films are deposited using a compound comprising a carbon-carbon double or carbon-carbon triple bond. The plasma source employed comprises both a remote plasma source and an in-situ plasma source operating in combination.

IPC 8 full level

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